

In th Sp cification

Please replace paragraph beginning at line 23 on page 7 with the following clean replacement paragraph. A marked-up version showing amendments to the specification paragraph being changed is provided in one or more accompanying pages separate from this amendment.

91 Other aspects of the invention are described with reference to Figs. 2 through 4. Fig. 2 illustrates a field emission device in the form of field emission display 40 in fabrication. In the depicted example, such comprises an electron emitter substrate 42 formed of a glass plate 44 having a first semiconductive material 46 formed thereover. Semiconductive material 46 might comprise either a p-type doped or an n-type doped semiconductive material (such as, for example, monocrystalline silicon). Emitters 48 are provided in electrical connection with layer 46, and preferably comprise a second semiconductive material, for example doped polycrystalline silicon. Exemplary dielectric regions 50, such as borophosphosilicate glass, are provided over material 46 and intermediate emitters 48. An electrically conductive extraction grid 52 is provided over dielectric material 50 and accordingly is outwardly of and spaced from emitters 48.
